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| <b>FORM PTO-1449</b>   |  | Atty. Docket No.:<br>B784.312-0001          | Application No.:<br>10/017,734 |
| <b>LIST OF PATENTS AND PUBLICATIONS FOR<br/>APPLICANT'S INFORMATION<br/>DISCLOSURE STATEMENT</b> |  | First Named Inventor:<br>Baowei KANG et al. |                                |
|  |  | Filing Date:<br>December 7, 2001            | Group Art:<br>2826 2823        |

**U.S. PATENT DOCUMENTS**

| Examiner Initial | Document No. | Date | Name | Class | Sub Class | Filing Date If Appropriate |
|------------------|--------------|------|------|-------|-----------|----------------------------|
| AA               |              |      |      |       |           |                            |
| AB               |              |      |      |       |           |                            |
| AC               |              |      |      |       |           |                            |
| AD               |              |      |      |       |           |                            |
| AE               |              |      |      |       |           |                            |
| AF               |              |      |      |       |           |                            |

**FOREIGN PATENT DOCUMENTS**

|  |    | Document No. | Date | Country | Class | Sub Class | Translation<br>Yes No |
|--|----|--------------|------|---------|-------|-----------|-----------------------|
|  | AG |              |      |         |       |           |                       |
|  | AH |              |      |         |       |           |                       |
|  | AI |              |      |         |       |           |                       |

**OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)**

|             |    |  |
|-------------|----|--|
| <u>K.N.</u> | AJ | Hideo Iwamoto et al., "A New Punch-Through IGBT Having a New n-Buffer Layer", IEEE TRANSACTIONS ON INDUSTRY APPLICATIONS, Vol. 38, No. 1, January/February 2002, pp. 168-174.                  |
| <u>K.N.</u> | AK | T. Laska et al., "Optimizing the Vertical IGBT Structure - The NPT Concept as the Most Economic and Electrically Ideal Solution for a 1200V-IGBT", Proceedings of the ISPSD 1996, pp. 169-172. |
| <u>K.N.</u> | AL | Darryl Burns et al., "NPT-IGBT - Optimizing for Manufacturability", Proceedings of the ISPSD 1996, pp. 331-334.]   |
| <u>K.N.</u> | AM | K. Mochizuki et al., "Examination of Punch Through IGBT(PT-IGBT) for High Voltage and High Current Applications", PROCEEDINGS of the ISPSD 1997, pp. 237-240.                                  |
| <u>K.N.</u> | AN | G. Miller et al., "A New Concept for a Non Punch Through IGBT with MOSFET Like Switching Characteristics", 20th Annual IEEE Power Electronics Specialists Conference, 1989, pp. 21-25.         |
| <u>K.N.</u> | AO | B. J. Baliga et al., "The Insulated Gate Rectifier (IGR): A New Power Switching Device", IEDM Technical Digest, 1982, pp. 264-267.   |

EXAMINER: Khienguyen DATE CONSIDERED: 03/22/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.